

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









### MURT10040 thru MURT10060R

## Silicon Super Fast Recovery Diode

 $V_{RRM} = 50 \text{ V} - 600 \text{ V}$   $I_F = 100 \text{ A}$ 

#### **Features**

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

**Three Tower Package** 



### Maximum ratings, at T<sub>i</sub> = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MURT10040 (R)	MURT10060 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		400	600	V
RMS reverse voltage	$V_{RMS}$		283	424	V
DC blocking voltage	$V_{DC}$		400	600	V
Continuous forward current	$I_{F}$	T <sub>C</sub> ≤ 140 °C	100	100	Α
Surge non-repetitive forward current, Half Sine Wave	I <sub>F,SM</sub>	$T_C = 25  ^{\circ}C,  t_p = 8.3  \text{ms}$	400	400	А
Operating temperature	Tj		-40 to 175	-40 to 175	°C
Storage temperature	T <sub>stg</sub>		-40 to 175	-40 to 175	°C

### Electrical characteristics, at Tj = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MURT10040 (R)	MURT10060 (R)	Unit
Diode forward voltage	$V_{F}$	I <sub>F</sub> = 50 A, T <sub>j</sub> = 25 °C	1.35	1.7	V
Reverse current	I <sub>R</sub>	$V_R = 50 \text{ V}, T_j = 25 ^{\circ}\text{C}$	25	25	μA
		$V_R = 50 \text{ V}, T_j = 125 ^{\circ}\text{C}$	1	1	mA
Recovery Time					
Maximum reverse recovery time	T <sub>RR</sub>	I <sub>F</sub> =0.5 A, I <sub>R</sub> =1.0 A, I <sub>RR</sub> = 0.25 A	90	110	nS
Thermal characteristics					
Thermal resistance, junction - case	$R_{\text{thJC}}$		0.21	0.21	°C/W





## MURT10040 thru MURT10060R







